



JFW

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re the Application of:

Sang-jin PARK et al.

Art Unit: 2818

Serial No. 10/830,119

Examiner: Mai Huong C. Tran

Filed: April 23, 2004

*Confirmation No. 9008*

For: MAGNETIC RANDOM ACCESS MEMORY  
INCLUDING MIDDLE OXIDE LAYER AND  
METHOD OF MANUFACTURING THE  
SAME

Attorney Docket No. 249/464

**AMENDMENT UNDER 37 C.F.R. § 1.111**

Mail Stop Amendment  
Commissioner for Patents  
United States Patent and Trademark Office  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

**INTRODUCTORY COMMENTS**

In response to the Office action dated September 22, 2005, the following amendments and remarks are respectfully submitted in connection with the above-identified application:

**Amendments to the Specification** are reflected beginning on page 2 of this paper;

**Amendments to the Claims** are reflected in a listing of claims, which begins on page 3 of this paper.

**Remarks** begin on page 7 of this paper.